

ABSTRACT OF THE DISCLOSURE

A method for fabricating a plurality of semiconductor bodies, in particular based on nitride compound semiconductor material. The method includes forming a mask layer (3) over a substrate (1) or over an initial layer (2), which mask layer has a plurality of windows (4) leading to the substrate (1) or to the initial layer (2), etching back the substrate (1) or the initial layer (2) in the windows (4), in such a manner that pits (41) are formed in the substrate (1) or in the initial layer (2) starting from these windows. The semiconductor material (5) is grown onto the substrate (1) or onto the initial layer (2), in such a manner that lateral growth is promoted and the semiconductor material initially grows primarily from the flanks (43) of the pits (41) toward the center (42) of the pits (41) where they form a coalescence region (61), so that defects in the substrate (1) or in the initial layer (2) which impinge on the flanks (43) of the pits (41) bend off toward the center of the pits (41) in the semiconductor material, and then, starting from the windows (4), the semiconductor material grows over the mask layer (3) and grows together over the mask layer (3) between adjacent windows (4), where it forms a further coalescence region (62). A component layer sequence (8) is grown onto the semiconductor material (5).